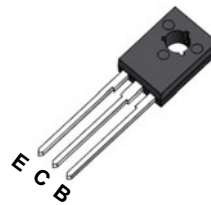


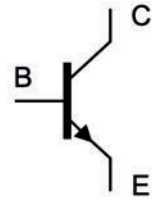
MJE340 NPN Power Transistor

Features

- Collector-emitter sustaining voltage $V_{CEO(SUS)}=260V$ (Min)
- DC current gain $h_{FE}=30$ (Min) @ $I_C=50mA$
- Low collector saturation voltage $V_{CE(sat)}=1.0V$ (Max.) @ $I_C=50mA$
- Complement to the PNP MJE350
- Minimum Lot-to-Lot variations for robust device performance and reliable operation



TO-126



Schematic Diagram

Applications

- Designed for high voltage and general purpose applications.

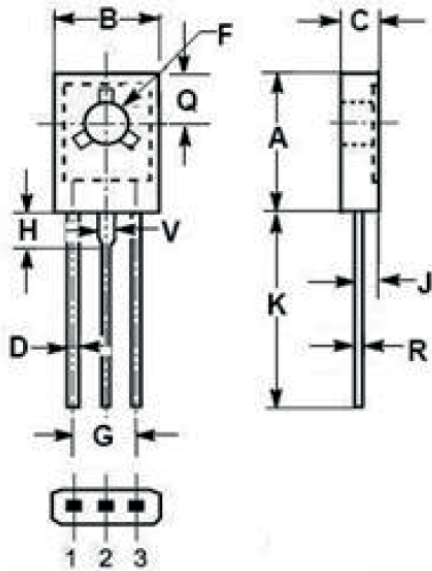
Absolute Maximum Ratings ($T_A=25^{\circ}C$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	260	V
Collector-Emitter Voltage	V_{CEO}	260	V
Emitter-Base Voltage	V_{EBO}	3	V
Collector Current-Continuous	I_C	0.5	A
Collector Power Dissipation $T_C=25^{\circ}C$	P_C	20	W
Junction Temperature	T_J	150	$^{\circ}C$
Storage Temperature Range	T_{stg}	-65 to +150	$^{\circ}C$
Thermal Resistance, Junction to Case	R_{thj-c}	6.25 (Max)	$^{\circ}C/W$

Electrical Characteristics ($T_C=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Conditions	Min	Max	Unit
Collector-Emitter Sustaining Voltage	$V_{CEO(SUS)}$	$I_C=1.0mA, I_B=0$	260	-	V
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C=1.0mA, I_E=0$	260	-	V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E=1.0mA, I_C=0$	3	-	V
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=50mA, I_B=5mA$	-	1.0	V
Collector Cutoff Current	I_{CBO}	$V_{CB}=260V, I_E=0$	-	0.1	mA
Emitter Cutoff Current	I_{EBO}	$V_{EB}=3V, I_C=0$	-	0.1	mA
DC Current Gain	h_{FE}	$I_C=50mA, V_{CE}=10V$	30	240	-

Package Outline Dimensions (TO-126)



- PIN
1. Emitter
 2. Collector
 3. Base

Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	10.70	10.95	0.421	0.431
B	7.70	7.90	0.303	0.311
C	2.60	2.80	0.102	0.110
D	0.66	0.86	0.026	0.034
F	3.10	3.30	0.122	0.130
G	4.48	4.68	0.176	0.184
H	2.00	2.20	0.079	0.087
J	1.35	1.55	0.053	0.061
K	15.30	16.30	0.602	0.642
Q	3.70	3.90	0.146	0.154
R	0.40	0.60	0.016	0.024
V	1.17	1.37	0.046	0.054